

ABSTRACT OF THE DISCLOSURE

In a crystallization process of an amorphous semiconductor film, a first crystalline semiconductor film having crystalline regions, and dotted with amorphous regions within the crystalline regions, is obtained by performing heat treatment processing after introducing a metallic element which promotes crystallization on the amorphous semiconductor film. The amorphous regions are kept within a predetermined range by regulating the heat treatment conditions at this point. Laser annealing is performed on the first crystalline semiconductor film, to form a second crystalline semiconductor film. Electrical characteristics for a TFT manufactured based on the second crystalline semiconductor film can be obtained having less dispersion.